

**SPECIFICATION OF LED CHIP**  
**C850-40P**  
**[INFRARED]**

1) Commodity Type and Physical Characteristics.

- |                      |                     |                             |
|----------------------|---------------------|-----------------------------|
| 1. Material          | GaAlAs/GaAlAs (DDH) |                             |
| 2. Electrode         | Top Side            | N (cathode) side : Au Alloy |
|                      | Bottom Side         | P (anode) side : Au Alloy   |
| 3. Electrode Pattern | Fig.1               |                             |
| 4. Chip Size         | Fig.2               |                             |
| 5. Chip Thickness    | Fig.2               |                             |
| 6. Emission Area     | Fig.2               |                             |

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	Vf	If=20mA		1.5	1.7	V
Reverse Current	Ir	Vr=5V			10	uA
Power Intensity	Po	If=20mA	2.5	4.0		mW
Peak Wavelength	$\lambda_P$	If=20mA	835	850	865	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	If=20mA		35		nm
RiseTime	tr	If=20mA		80		ns
FallTime	tf	If=20mA		60		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(Ta=25 )

[Unit : um]

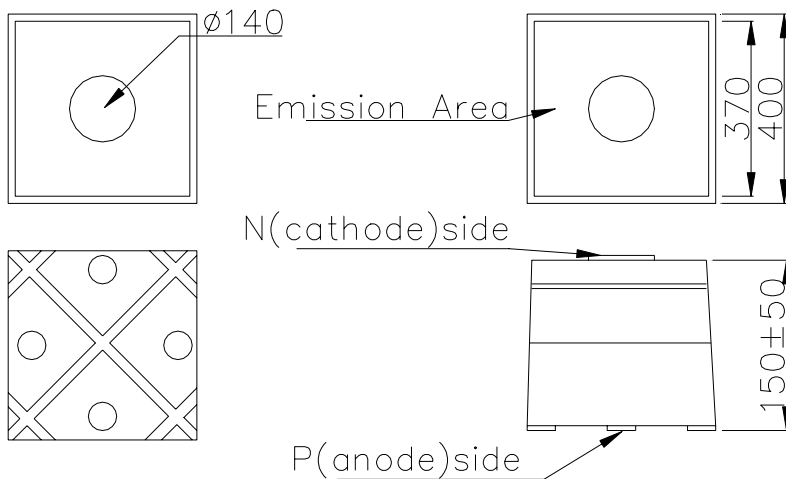


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area